Abstract

The present invention provides a method for manufacturing a bonded wafer prepared by bonding a base wafer and a bond wafer, comprising at least a step of etching an oxide film in a terrace region in an outer periphery of the bonded wafer wherein the oxide film in the terrace region is etched by spin-etching with holding and spinning the bonded wafer. Thereby, there is provided a method for manufacturing a bonded wafer in which an oxide film formed in a terrace region of a base wafer is efficiently etched without removing an oxide film on the back surface of the base wafer.